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February 15, 2005

09/675578

Commissioner for Patents  
PO Box 1450  
Alexandria, VA 22313-1450

Certificate  
JUN 08 2005  
of Correction

Re: **CERTIFICATE OF CORRECTION**  
U. S. Letters Patent No. 6,839,823  
Issued: January 4, 2005  
For: INCREASED RELIABILITY OF DATA  
STORED ON FLASH MEMORY IN  
APPLICATIONS SENSITIVE TO  
POWER-LOSS  
Inventor: See et al.  
Our File No. 42390.P4487x

Dear Sir:

Enclosed is the Certificate of Correction (two copies) for the above-referenced patent. Also enclosed is a copy of the original application and corresponding postcard dated September 29, 2000. Please see the previous correction and a copy of the original application indicating that the page number was scanned in.

This request for correction is made under rule 322 of the Rules of Practice and 35 U.S.C. Section 254.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

  
Edwin H. Taylor  
Reg. No. 25,129

EHT/jsq  
Enclosures

UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION

PATENT NO. : 6,839,823

DATED : January 4, 2005

INVENTOR(S) : See et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In column 3, at line 4, delete "6".

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MAILING ADDRESS OF SENDER  
BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN  
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PATENT NO. 6,839,823

**Certificate of Correction (PTO Form 1050)-Amended**

UNITED STATES PATENT AND TRADEMARK OFFICE  
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OCT 10 2000

BLAKELY, SOKOLOFF, MILLER & ZAFMAN  
LOS ANGELES

Serial/Patent No.: \*\*\*\*\* Filing/Issue Date: 9/29/00

Client: INTEL CORPORATION

Title: INCREASED RELIABILITY OF DATA STORED ON FLASH MEMORY IN  
APPLICATIONS SENSITIVE TO POWER-LOSS

BSTZ File No.: 42390 P4487X

Atty/Secty Initials: LJV/MSK/jb

Date Mailed: 9/29/00

Docket Due Date:

The following has been received in the U.S. Patent & Trademark Office on the date stamped hereon:

- Amendment/Response (\_\_\_\_ pgs.)
- Appeal Brief (\_\_\_\_ pgs.) (in triplicate)
- Application - Utility (\_\_\_\_ pgs., with cover and abstract)
- Application - Rule 1.53(b) Continuation (\_\_\_\_ pgs.)
- Application - Rule 1.53(b) Divisional (\_\_\_\_ pgs.)
- Application - Rule 1.53(b) CIP (24 pgs.)
- Application - Rule 1.53(d) CPA Transmittal (\_\_\_\_ pgs.)
- Application - Design (\_\_\_\_ pgs.)
- Application - PCT (\_\_\_\_ pgs.)
- Application - Provisional (\_\_\_\_ pgs.)
- Assignment and Cover Sheet
- Certificate of Mailing
- Declaration & POA (4 pgs.)
- Disclosure Docs & Ctg & Copy of Inventor Signed Letter (\_\_\_\_ pgs.)
- Drawings: 23 # of sheets includes 24 figures

- Express Mail No.: EL672752482US  Check No. 31923
- \_\_\_\_\_ Month(s) Extension of Time  Amt: 640
- Information Disclosure Statement & PTO-149 (\_\_\_\_ pgs.)  Check No. \_\_\_\_\_
- Issue Fee Transmittal  Amt. \_\_\_\_\_
- Notice of Appeal  Check No. \_\_\_\_\_
- Petition for Extension of Time  Amt. \_\_\_\_\_
- Petition for \_\_\_\_\_  Check No. \_\_\_\_\_
- Postcard  Amt. \_\_\_\_\_
- Power of Attorney (\_\_\_\_ pgs.)  Check No. \_\_\_\_\_
- Preliminary Amendment (\_\_\_\_ pgs.)  Amt. \_\_\_\_\_
- Reply Brief (\_\_\_\_ pgs.)  Check No. \_\_\_\_\_
- Response to Notice of Missing Parts  Amt. \_\_\_\_\_
- Small Entity Declaration for Indep. Inventor/Small Business  Check No. \_\_\_\_\_
- Transmittal Letter, in duplicate (Qx2 pg.)  Amt. \_\_\_\_\_
- Fee Transmittal, in duplicate (Qx2 pg.)  Amt. \_\_\_\_\_

Other: \_\_\_\_\_

0/11/2000

Due date

12/29/2000

Client Name Intel Corporation

Docket Initial

42390 . P4487X

Docket Sup. Initial

LJV MSK

Atty/Initial

Pat/Ser/Reg 675,578

19

Description

month deadline to file prior art disclosure and check related cases  
based on filed US application).



Attorney's Docket No. 042390.P4487X

PATENT

UNITED STATES PATENT APPLICATION

FOR

INCREASED RELIABILITY OF DATA STORED ON FLASH MEMORY IN  
APPLICATIONS SENSITIVE TO POWER-LOSS

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EL672752482US

"Express Mail" mailing label number

9/29/00

Date of Deposit

I hereby certify that I am causing this paper or fee to be deposited with the United States Postal Service "Express Mail Post Office to Addressee" service on the date indicated above and that this paper or fee has been addressed to the Assistant Commissioner for Patents, Washington, D. C. 20231

JUANITA BK ISCOE  
(Typed or printed name of person mailing paper or fee)

Robert N. Hasbun  
(Signature of person mailing paper or fee)



## INCREASED RELIABILITY OF DATA STORED ON FLASH MEMORY IN APPLICATIONS SENSITIVE TO POWER-LOSS

### CROSS-REFERENCED RELATED APPLICATION

5 This application is Continuation-in-Part of U.S. Patent Application No. 09/063,954 entitled, "DYNAMIC ALLOCATION FOR EFFICIENT MANAGEMENT OF VARIABLE SIZED DATA WITHIN A NONVOLATILE MEMORY," filed on April 21, 1998.

### 10 FIELD OF THE INVENTION

The present relates to computer memory storage systems. More particularly, the present invention relates to dynamic allocation for efficient management of variable sized data within a nonvolatile memory. Specifically, the present relates to increased reliability of data stored on flash memory in applications sensitive to power-loss.

15

### BACKGROUND OF THE INVENTION

Communications devices such as cellular telephones and pagers need the ability to store both data and code. In addition, these communications devices typically require some sort of working memory.

20 These communication devices generally need to store the code and at least some of the data in nonvolatile memory. For example, serial numbers, authorization codes, frequently dialed numbers, etc. are examples of data that might be stored in nonvolatile memory. Given that the code and data are updated at different frequencies, the communications devices often used different types of nonvolatile memory for storage of  
25 data and code. As a result, prior art communications devices typically included one type

of nonvolatile memory for code storage, another nonvolatile memory for data storage, and random access memory such as static random access memory for working memory.

One type of nonvolatile memory is a flash electrically erasable programmable read only memory (flash EEPROM). Flash EEPROM (hereinafter "flash memory") is 5 typically arranged as blocks of single transistor memory cells. Although flash memory is rewritable, the memory cells cannot be re-programmed unless they have first been erased. Moreover, the cells are erasable only in blocks. Thus in order to erase one cell, an entire block of cells must be erased. Updating the flash memory requires some form of media manager to handle copying of valid information out of the block, erasing the block, and 10 writing the valid information as well as the update information to the same or another block. The process of erasing, writing, etc. is relatively time consuming.

Another type of nonvolatile memory is an electrically erasable programmable read only memory (EEPROM) having two-transistor memory cells. Although EEPROM may be arranged into erasable blocks similar to the flash memory, the two-transistor EEPROM 15 is relatively easy to update and does not require the sophisticated media management that flash memory requires for updates. Writing a value to the two-transistor EEPROM cell, however, requires significantly greater time than does programming of an erased single transistor flash memory cell.

One prior art communications device memory architecture includes flash memory 20 for code storage, EEPROM for data storage, and random access memory as working memory.

The use of a variety of nonvolatile memories tends to increase form factor size as well as design and fabrication costs. Personal communications devices such as pagers and cellular telephones are often differentiated based on their size, features, cost, and rate 25 of power consumption.

Moreover as new features are constantly being added, the ratio of code to data may need to change. Providing excess storage for both types of nonvolatile memory increases the cost of the device and is wasteful, unless the storage requirements for both the code and the data are expected to grow. By storing code and data into different types of nonvolatile memory, excess storage capacity in the nonvolatile memory used for code is unavailable for storing data. Similarly, excess storage capacity in the nonvolatile memory used for data is unavailable for storing code. Thus the design is unable to easily accommodate changes in the ratio of nonvolatile memory allocated to code versus that allocated to data.

Furthermore, a common concern with operating a nonvolatile memory device such as a flash memory is power-loss. That is, a sudden loss of power may cause data in the non-volatile memory to be lost or unreliable. Thus, a nonvolatile memory device must be able to recover and to determine the reliability of data in the memory device after a power-loss.

## **BRIEF DESCRIPTION OF THE DRAWINGS**

The present invention is illustrated by way of example and not intended to be limited by the figures of the accompanying drawings, in which like references indicate similar elements and in which:

5       Figure 1 illustrates storage of code and data in the same monolithic nonvolatile memory device;

Figure 2 illustrates the storage of objects within a block of the nonvolatile memory;

Figure 3 illustrates an object header structure;

10      Figure 4 illustrates a multiple instance storage structure;

Figure 5 illustrates a sequence table entry and status values;

Figure 6 illustrates the use of a sequence table for identifying the order and location of associated data fragments;

15      Figure 7 illustrates the use of a group table for identifying the order and location of associated sequence table fragments;

Figure 8 illustrates a method of creating the data lookup table;

Figure 9 illustrates a method of selecting a storage structure in accordance with the size ( $z$ ) of the data with respect to a plurality of thresholds including: a minimum number of instances ( $m$ ); an allocation granularity ( $g$ ); a maximum single instance size ( $s*g$ ); and a maximum sequence table size;

Figure 10 illustrates a method of writing a single instance object;

Figures 11-12 illustrate a method of writing a multiple instance object;

Figures 13-15 illustrate a method of storing an object as a plurality of data fragments;

Figure 16 illustrates a method for appending to a fragmented object when sufficient room is available in the last sequence table fragment;

Figures 17-19 illustrates a method for replacing selected fragments of a fragmented object;

5       Figure 20 illustrates a method for reclaiming space within the nonvolatile memory;

Figure 21 illustrates a flash memory system;

Figure 22 illustrates a timing diagram for a flash memory system causing storage of invalid data;

10      Figure 23 illustrates a new data header having redundant power-loss status fields to deal with power-loss; and

Figure 24 illustrates a method for duplicating power-loss status fields.

## DETAILED DESCRIPTION

Figure 1 illustrates the storage of both code and data in a monolithic nonvolatile memory device 110. In one embodiment, the nonvolatile memory comprises a plurality of individually erasable blocks. The amount of space allocated to the data and code portions may span one or more blocks as long as the data and code portion do not share a same block.

Nonvolatile memory device 110 has a boot code 112 portion, a data storage 114 portion, a spare block 116, and a code storage 118 portion. The spare block 116 is an actual physical block of the nonvolatile memory device. As will be described below, 10 logical block numbers are used so that the spare block can be any physical block within the data portion 114.

Spare block 116 is used during the reclamation process to recover the valid contents of another block before erasing that other block to free up the space used by invalid contents. Due to the characteristics of flash memory and the relatively long time 15 required to erase a block, superseding data is written to a new location within the nonvolatile memory. The older version of the data is invalidated and the space associated with the invalid data can subsequently be reclaimed by erasing the block after copying any valid data in the block to the spare block. After erasure, the erased block becomes the new spare block.

20 Figure 2 indicates how data is identified and stored within one of the individual blocks allocated to the data storage 114 portion of Figure 1. The minimal amount of space that can be allocated is referred to as the unit granularity, or simply granularity. The data to be stored is allocated into individual areas spanning one or more units of granularity. Each of these areas is referred to as an object. For example, block 210 25 includes objects 1, 2, and 3. Each object within the block is identified by an object



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BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP  
LOS ANGELES

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MCL

Request for Certificate of Correction:

Consideration has been given your request for the issuance of a certificate of correction for the above-identified patent under the provisions of Rules 1.322.

Respecting the alleged error in column 3, line 4 can not be found. Therefore, no correction(s) is in order here under United States Codes (U.S.C.) 254 Code of Federal Regulation (C.F.R.) 1.322.

In view of the foregoing, your request is hereby denied. A Certificate of Correction will issue for all other matters.

Further consideration will be given upon receipt of a Request for Reconsideration, which should be directed to Decisions and Certificate of Correction Branch. Requests for Reconsideration should be accompanied by additional support (e.g. copy of amendments, post card receipts. PTOL 1449 OR 892, etc.), containing requested data or changes) and /or brief statements of facts, as requested.

RoChawn Johnson for  
Cecelia Newman, Supervisor  
Decisions and Certificates of Correction  
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*The page  
was scanned in.  
GPT*



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